

## UNISONIC TECHNOLOGIES CO., LTD

01N60Z-ML Preliminary Power MOSFET

# 0.1A, 600V N-CHANNEL POWER MOSFET

#### **■** DESCRIPTION

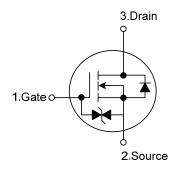
The UTC **01N60Z-ML** is a N-channel mode power MOSFET using UTC's advanced technology to provide customers with a minimum on-state resistance, high switching speed, low gate charge and low input capacitance.

The UTC **01N60Z-ML** is universally applied in high efficiency switch mode power supply.

#### **■ FEATURES**

- \*  $R_{DS(ON)} \le 60 \Omega$  @  $V_{GS}=10V$ ,  $I_D=50mA$
- \* High switching speed
- \* With ESD protection

#### ■ SYMBOL



#### ■ ORDERING INFORMATION

Ordering Number		Dookona	Pin Assignment			Dealine	
Lead Free	Halogen Free	Package	1	2	3	Packing	
01N60ZL-AE2-R	01N60ZG-AE2-R	SOT-23-3	G	S	D	Tape Reel	

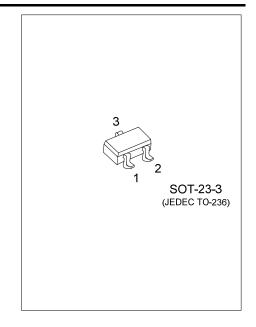
Note: Pin Assignment: G: Gate S: Source D: Drain

01N60ZG-AE2-R

(1)Packing Type
(2)Package Type
(3)Green Package
(3) G: Halogen Free and Lead Free, L: Lead Free

#### ■ MARKING





<u>www.unisonic.com.tw</u> 1 of 5

### ■ **ABSOLUTE MAXIMUM RATINGS** (T<sub>C</sub>=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		$V_{DSS}$	600	V	
Gate-Source Voltage (Note 2)		$V_{GSS}$	±20	V	
Drain Current	Continuous	I <sub>D</sub>	0.1	Α	
	Pulsed	I <sub>DM</sub>	0.3	Α	
Power Dissipation(Ta=25°ℂ)		$P_D$	0.5	W	
Junction Temperature		TJ	+150	°C	
Storage Temperature		T <sub>STG</sub>	-55 ~ <b>+</b> 150	°C	

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

## **■ THERMAL DATA**

PARAMETER	SYMBOL	RATINGS	UNIT	
Junction to Ambient	$\theta_{JA}$	250	°C/W	
Junction to Case	θ <sub>JC</sub>	208	°C/W	

Note: Device mounted on FR-4 substrate Pc board, 2oz copper, with 1inch square copper plate.

## ■ **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub>=25°C, unless otherwise specified)

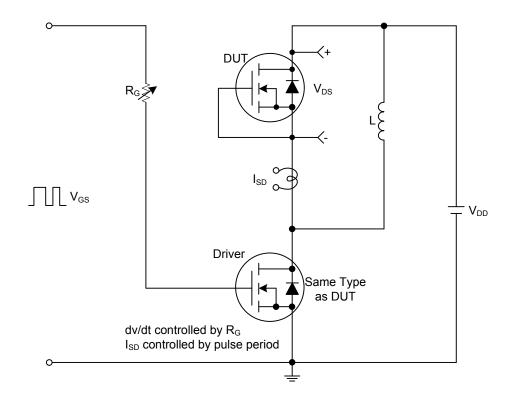
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						•	
Drain-Source Breakdown Voltage		BV <sub>DSS</sub>	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	600			V
Drain-Source Leakage Current		I <sub>DSS</sub>	V <sub>DS</sub> =600V			10	μΑ
Gate-Source Leakage Current	Forward	I <sub>GSS</sub>	V <sub>GS</sub> =20V, V <sub>DS</sub> =0V			10	uA
	Reverse		V <sub>GS</sub> =-20V, V <sub>DS</sub> =0V			-10	uA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	$V_{DS}=V_{GS}$ , $I_D=250\mu A$			4.0	V
Static Drain-Source On-State Resistance		R <sub>DS(ON)</sub>	$V_{GS}$ =10V, $I_D$ =50mA			60	Ω
DYNAMIC PARAMETERS							
Input Capacitance	put Capacitance		V <sub>GS</sub> =0V, V <sub>DS</sub> =25V,		27		pF
Output Capacitance		C <sub>ISS</sub> C <sub>OSS</sub>			11		pF
Reverse Transfer Capacitance		$C_{RSS}$	f=1.0MHz (Note 1, 2)		2.9		pF
SWITCHING PARAMETERS							
Total Gate Charge (Note 1)		$Q_G$			8.2		nC
Gate-Source Charge		$Q_GS$	$V_{DS}$ =100V, $V_{GS}$ =10V, $I_{D}$ =0.1A		2.9		nC
Gate-Drain Charge		$Q_GD$			1		nC
Turn-On Delay Time (Note 1)		t <sub>D(ON)</sub>	\\ -100\\ \\ -10\\		4.4		ns
Turn-On Rise Time		$t_R$	$V_{DD}$ =100V, $V_{GS}$ =10V, $I_{D}$ =50mA, $R_{G}$ =3.3 $\Omega$		18		ns
Turn-Off Delay Time		t <sub>D(OFF)</sub>	(Note 1, 2)		20		ns
Turn-Off Fall Time		$t_{F}$	(NOLE 1, 2)		320		ns
SOURCE- DRAIN DIODE RATINGS	AND CHA	RACTERISTI	cs				
Maximum Body-Diode Continuous Current		Is				0.1	Α
Maximum Body-Diode Pulsed Current (Note 1)		I <sub>SM</sub>				0.3	Α
Drain-Source Diode Forward Voltage (Note 1)		$V_{SD}$	I <sub>S</sub> =0.1A, V <sub>GS</sub> =0V			1.4	<b>V</b>

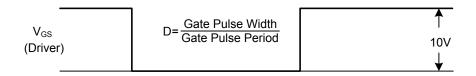
Notes: 1. Pulse Test: Pulse width ≤ 250µs, Duty cycle ≤ 2%

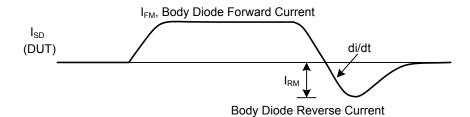
2. Essentially independent of operating temperature

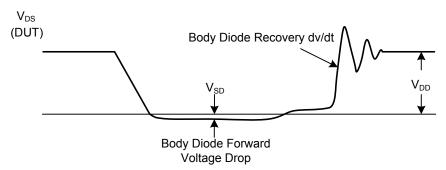
<sup>2.</sup> Repetitive Rating: Pulse width limited by maximum junction temperature.

## ■ TEST CIRCUITS AND WAVEFORMS



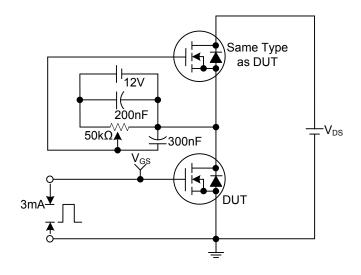


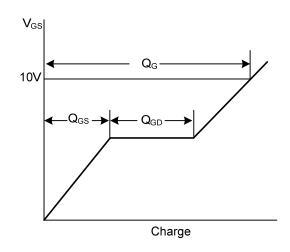




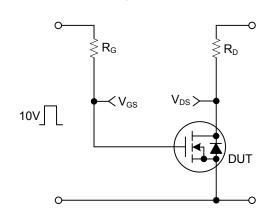
Peak Diode Recovery dv/dt Test Circuit and Waveforms

## ■ TEST CIRCUITS AND WAVEFORMS

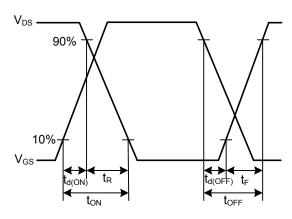




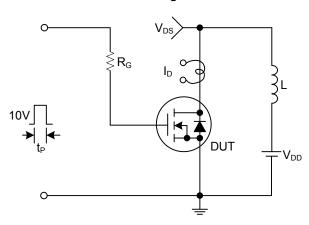
**Gate Charge Test Circuit** 



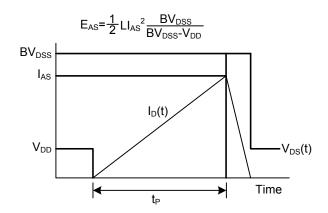
**Gate Charge Waveforms** 



**Resistive Switching Test Circuit** 



**Resistive Switching Waveforms** 



**Unclamped Inductive Switching Test Circuit** 

**Unclamped Inductive Switching Waveforms** 

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